

Typical Applications

Microwave Radio & VSAT

Telecom Infrastructure

• Military & Space

· Fiber optics

Test Instrumentation

The HMC994LP5E is ideal for:



v01.0314

HMC994LP5E

GaAs pHEMT MMIC POWER AMPLIFIER, DC - 28 GHz

Features

P1dB Output Power: +27 dBm Psat Output Power: +29 dBm High Gain: 13 dB Output IP3: +38 dBm Supply Voltage: Vdd = +10V @ 250 mA 50 Ohm Matched Input/Output 32 Lead 5x5 mm SMT Package: 25 mm²

General Description

The HMC994LP5E is a GaAs pHEMT MMIC Distributed Wideband Power Amplifier which operates between DC and 28 GHz. The amplifier provides 13 dB of gain, +29 dBm of saturated output power, and 23% PAE from a +10V supply. With up to +38 dBm Output IP3 the HMC994LP5E is ideal for high linearity applications in military and space as well as point-to-point and pointto-multi-point radios. The HMC994LP5E exhibits a very flat gain from 4 to 16 GHz making it ideal for EW, ECM, Radar and test equipment applications. The HMC994LP4E amplifier I/Os are internally matched to 50 Ohms and is packaged in a leadless QFN 5x5 mm surface mount package.

Functional Diagram ACG2 ACG1 N/C N/C 29 31 30 28 27 26 25 <u>∕24</u> N/C GND 1Vgg2 2 23 N/C N/C ____22 GND 3 RFOUT GND 4 21 & Vdd ____20 RFIN GND 5 N/C GND 6 _ 19 N/C 7 18 N/C N/C 8/ J7 N/C 1 14 5 2 2 13 6 N/C Vgg1 V/C N/C GND ACG4 ACG3 PACKAGE BASE GND

Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd = +10V, Vgg2 = +3.5V Idd = 250 mA^[1]

| Parameter | Min. | Тур. | Max. | Min. | Тур. | Max. | Min. | Тур | Max. | Units |
|--|---------|-------|---------|------|---------|------|------|-------|------|--------|
| Frequency Range | DC - 10 | | 10 - 20 | | 20 - 28 | | GHz | | | |
| Gain | 11 | 13 | | 11 | 13 | | 11 | 13 | | dB |
| Gain Flatness | | ±0.5 | | | ±0.5 | | | ±0.5 | | dB |
| Gain Variation Over Temperature | | 0.008 | | | 0.011 | | | 1.016 | | dB/ °C |
| Input Return Loss | | 18 | | | 15 | | | 12 | | dB |
| Output Return Loss | | 18 | | | 16 | | | 12 | | dB |
| Output Power for 1 dB Compression (P1dB) | 26 | 28 | | 24.5 | 27 | | 22.5 | 25 | | dBm |
| Saturated Output Power (Psat) | | 30 | | | 29.5 | | | 28 | | dBm |
| Output Third Order Intercept (IP3) [2] | | 41 | | | 37 | | | 35 | | dBm |
| Noise Figure | | 4 | | | 4 | | | 5 | | dB |
| Total Supply Current | | 250 | 300 | | 250 | 300 | | 250 | 300 | mA |

[1] Adjust Vgg1 between -2 to 0V to achieve Idd = 250 mA typical.

[2] Measurement taken at Pout / tone = +16 dBm.

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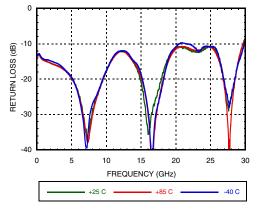


ROHS V

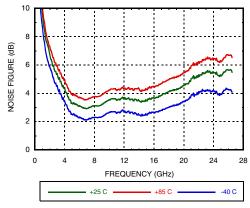
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Gain & Return Loss 20 10 RESPONSE (dB) 0 -10 -20 -30 -40 35 0 5 10 15 25 30 40 20 FREQUENCY (GHz) S22 S21 S11

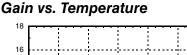
Input Return Loss vs. Temperature

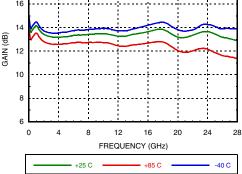


Noise Figure vs. Temperature

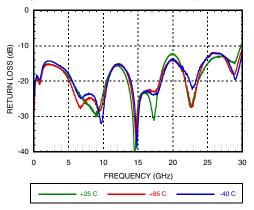


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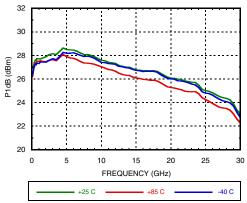




Output Return Loss vs. Temperature







AMPLIFIERS - LINEAR & POWER - SMT

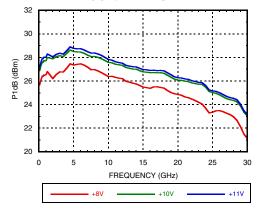
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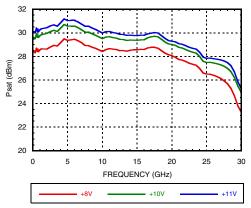
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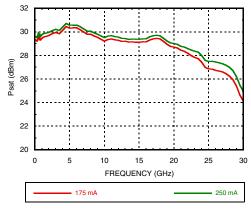
P1dB vs. Supply Voltage



Psat vs. Supply Voltage

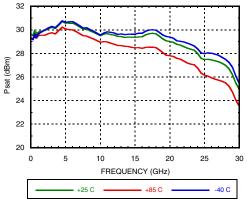


Psat vs. Supply Current

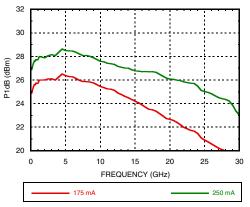


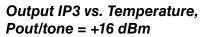


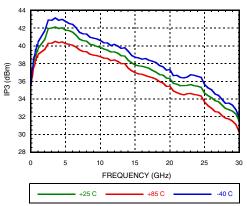




P1dB vs. Supply Current







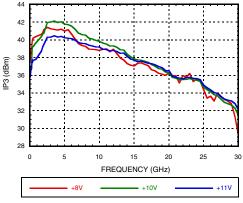
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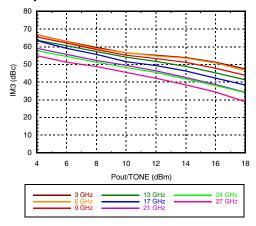
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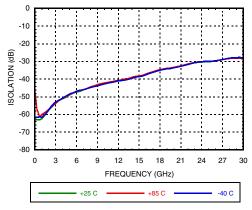
Output IP3 vs. Supply Voltage, Pout/tone = +16 dBm



Output IM3 @ Vdd =+10V

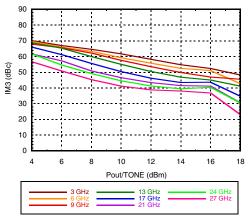


Reverse Isolation vs. Temperature

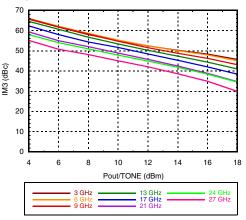


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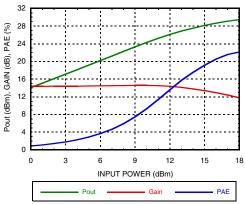
Output IM3 @ Vdd = +8V



Output IM3 @ Vdd = +11V



Power Compression @ 16 GHz



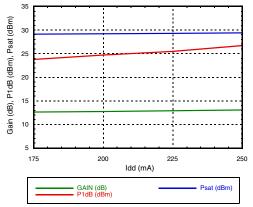
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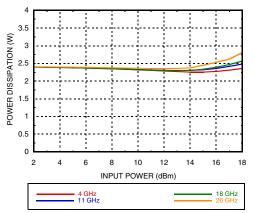
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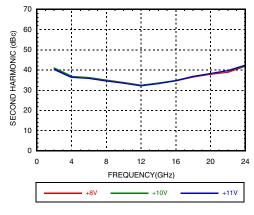
Gain & Power vs. Supply Current @ 16 GHz



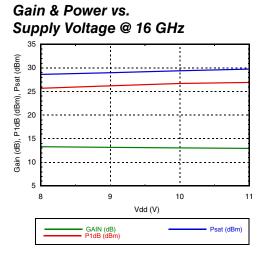
Power Dissipation



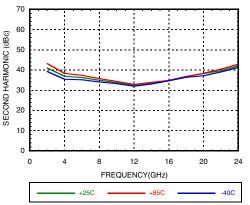
Second Harmonics vs. Vdd @ Pout = 14 dBm



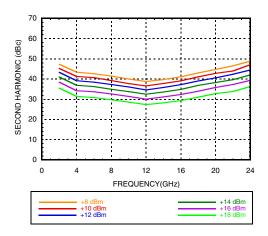
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Second Harmonics vs. Temperature @ Pout = 14 dBm



Second Harmonics vs. Pout



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Absolute Maximum Ratings

| | - |
|--|--|
| Drain Bias Voltage (Vdd) | +12 Vdc |
| Gate Bias Voltage (Vgg1) | -3 to 0 Vdc |
| | For Vdd = 12V, Vgg2 = 5.5V Idd < 200mA |
| Gate Bias Voltage (Vgg2) | For Vdd between 8.5V to 11V, Vgg2 = (Vdd - 6.5V) up to 4.5V |
| | For Vdd < 8.5V, Vgg2 must remain > 2V |
| RF Input Power (RFIN) | +25 dBm |
| Channel Temperature | 150 °C |
| Continuous Pdiss (T= 85 °C) (derate 46.1 mW/°C above 85 °C) | 3.0 W |
| Thermal Resistance (channel to ground paddle) | 21.6 °C/W |
| Storage Temperature | -65 to 150°C |
| Operating Temperature | -55 to 85 °C |
| ESD Sensitivity (HBM) | Class 1A |

GaAs pHEMT MMIC **POWER AMPLIFIER, DC - 28 GHz**

HMC994LP5E

Typical Supply Current vs. Vdd

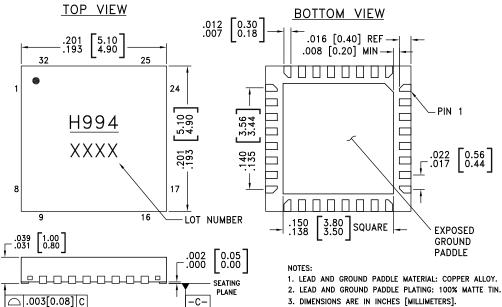
| Vdd (V) | ldd (mA) |
|---------|----------|
| +8 | 250 |
| +9 | 250 |
| +10 | 250 |
| +11 | 250 |

Adjust Vgg1 to achieve Idd = 250 mA



ELECTROSTATIC SENSITIVE DEVICE **OBSERVE HANDLING PRECAUTIONS**

Outline Drawing



- 3. DIMENSIONS ARE IN INCHES [MILLIMETERS].
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- 5. PAD BURR LENGTH SHALL BE 0.15mm MAX. PAD BURR HEIGHT SHALL BE 0.25mm MAX.
- 6. PACKAGE WARP SHALL NOT EXCEED 0.05mm
- 7. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

Package Information

| <u> </u> | | | | |
|-------------|--|---------------|---------------------------|--------------------------------|
| Part Number | Package Body Material | Lead Finish | MSL Rating ^[2] | Package Marking ^[1] |
| HMC994LP5E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 | <u>H994</u> XXXX |

[1] 4-Digit lot number XXXX

[2] Max peak reflow temperature of 260 °C

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Pin Descriptions

| Pin Number | Function | Description | Interface Schematic | |
|---|-------------|--|---------------------|--|
| 1, 4, 6, 14, 20, 22, Package Bottom | GND | These pins & exposed ground paddle must be con- nected to RF/DC ground. | | |
| 2 | VGG2 | Gate control 2 for amplifier. Attach bypass capacitor per application circuit herein. For nominal operation +3.5V should be applied to Vgg2 | VGG2O | |
| 3, 7, 8, 9, 10, 11, 12, 17, 18, 19, 23, 24, 25, 26, 27, 28, 31, 32 | N/C | No connection required. These pins may be con- nected to RF/DC ground without affecting perfor- mance. | | |
| 5 | RFIN | This pin is DC coupled and matched to 50 Ohms. Blocking capacitor is required. | | |
| 13 | Vgg1 | Gate control 1 for amplifier. Attach bypass capacitor per application circuit herein. Please follow "MMIC Amplifier Biasing Procedure" application note. | | |
| 15 | ACG4 | Low Frequency termination. Attach bypass capacitor | IN 0 | |
| 16 | ACG3 | per application circuit herein. | | |
| 21 | RFOUT & Vdd | RF output for amplifier. Connect DC bias (Vdd) net- work to provide drain current (Idd). See application circuit herein. | | |
| 29 | ACG2 | Low frequency termination. Attach bypass capacitor | ACG2O | |
| 30 | ACG1 | per application circuit herein | ± | |

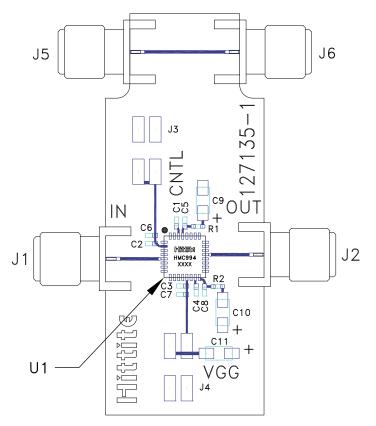


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GaAs pHEMT MMIC POWER AMPLIFIER, DC - 28 GHz

Evaluation PCB



Evaluation Order Information

| Item | Contents | Part Number |
|---------------------|---------------------------|----------------------------------|
| Evaluation PCB Only | HMC994LP5E Evaluation PCB | Eval01-HMC994LP5E ^[1] |

[1] Reference this number when ordering Evaluation PCB Only

List of Materials for Evaluation PCB EVAL01-HMC994LP5E

| Item | Description |
|--------------------|------------------------------|
| J1, J2, J5, J6 | PCB Mount SMA RF Connector |
| J3, J4 | DC Pins. |
| C1 - C4 | 1000 pF Capacitor, 0402 Pkg. |
| C5 - C8 | 10 kpF Capacitor, 0402 Pkg. |
| C9 - C11 | 4.7 uF Capacitor, Tantalum. |
| R1, R2 | 0 Ohm Resistor, 0402 Pkg. |
| U1 | HMC994LP5E |
| PCB ^[1] | 127135 Evaluation PCB. |

[1] Circuit Board Material: Rogers 4350 or Arlon 25FR

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

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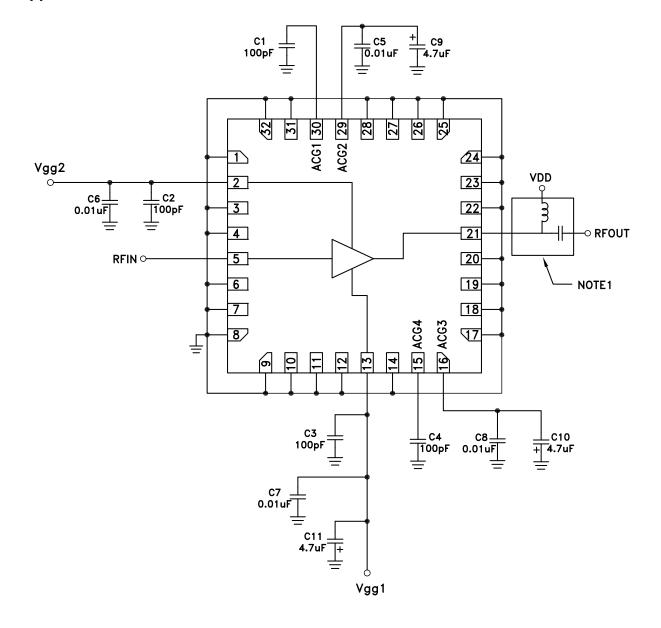
Application Circuit

HMC994LP5E

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GaAs pHEMT MMIC POWER AMPLIFIER, DC - 28 GHz



NOTE 1: Drain Bias (Vdd) must be applied through a broadband bias tee or external bias network.

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Notes

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